

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IRFSL52N15D

D(2)

pin 1, Gate

3

2, Drain

3. Source

• FEATURES

- Static drain-source on-resistance: RDs(on)≤32mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

• High frequency DC-DC converters

• ABSO	LUTE MAXIMUM RATINGS(Ta=25°C	1 Z 3, source TO-262 package		
SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage	150	V	
V _{GS}	Gate-Source Voltage	±30	V	
١ _D	Drain Current-Continuous	51	A	
Юм	Drain Current-Single Pulsed	240	A	DIM MIN MAX
PD	Total Dissipation @T _c =25℃	230	W	A 4.37 4.77 A1 1.22 1.42 A2 2.47 2.87 b 0.70 0.97
Tj	Max. Operating Junction Temperature	175	°C	b2 1.17 1.42 c 0.28 0.53 D 23.20 24.02 D1 8.38 8.90
T _{stg}	Storage Temperature	-55~175	°C	D2 6.00 - E 9.90 10.39 E4 7.30 - e 2.54BSC
• THER	MAL CHARACTERISTICS	G 1.25 1.50 H2 - 1.31 L 13.34 14.10		
SYMBOL	PARAMETER	МАХ	UNIT	L1 3.30 4.06 L3 0.95 1.15
Rth(j-c)	Channel-to-case thermal resistance	0.47	°C/W	-

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ELECTRICAL CHARACTERISTICS

T_c=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =250 μ A	150			v
V _{GS} (th)	Gate Threshold Voltage	VDS=VGS; I _D =250	3		5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =36A			32	mΩ
I _{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =150V; V _{GS} = 0V			25	μA
V _{SD}	Diode forward voltage	I _s =36A, V _{GS} = 0V			1.5	V



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